Polarization Engineering *through* Nanoengineered Morphology

PENNSTATE

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Control of

- Intensity
- Operating frequency band
- Polarization state



Long History

- Intensity
- Operating frequency band

Short History

- Polarization state



Polarization

- Discovered in 1809



Etienne-Louis Malus 1775 - 1812



Polarization

- Discovered in 1809



Etienne-Louis Malus 1775 - 1812

– "Do not disturb" designs



Polarization Engineering

- Anisotropic materials
- Uniaxial and biaxial crystals
- Piezoelectric materials

- Bianisotropic materials
- Chiral materials
- Magnetoelectric materials



Polarization Engineering

- Anisotropic materials
- Bianisotropic materials





Introduction to Complex Mediums for Optics and Electromagnetics

Editors: Werner S. Weiglhofer • Akhlesh Lakhtakia





Polarization Engineering

Sculptured Thin Films

Sculptured Thin Films

Nanoengineered Morphology and Optics

Akhlesh Lakhtakia Russell Messier

SPIE Press (2005)

Students & Collaborators

- Joseph Sherwin, Sean Pursel, Benjamin Ross, Fei Wang (Penn State)
- Mark Horn, Jian Xu (Penn State)
- Ian Hodgkinson (Otago)
- Martin McCall (Imperial)
- John Polo (Edinboro)



Outline

- Introduction
- Optical Modeling
- Examples of Polarization Engineering
- More Examples
- What's next?



INTRODUCTION









Assemblies of Parallel Curved Nanowires/Submicronwires

Controllable Nanowire Shape

2-D - nematic3-D - helicoidal*combination morphologies*







Assemblies of Parallel Curved Nanowires/Submicronwires

Controllable Nanowire Shape

 2-D - nematic
 3-D - helicoidal combination morphologies
 vertical sectioning







Sculptured Thin Films

Assemblies of Parallel Curved Nanowires/Submicronwires

Controllable Nanowire Shape

2-D - nematic
 3-D - helicoidal
 combination morphologies vertical sectioning

Nanoengineered Materials (1-3 nm clusters)

Controllable Porosity (10-90 %)



Sculptured Thin Films

Antecedents:

- (i) Young and Kowal 1959
- (ii) Niuewenhuizen & Haanstra 1966
- (iii) Motohiro & Taga 1989

Conceptualized by Lakhtakia & Messier (1992-1995)

Optical applications (1992-)

Biological applications (2003-)



Sculptured Thin Films

Collaborators:

(i) Weiglhofer, University of Glasgow (ii) Robbie & Brett, University of Alberta (iii) McCall, Imperial College London (iv) Hodgkinson, University of Otago (v) Polo, Edinboro University (vi) Reyes, UNAM, Mexico (vii) Penn State Colleagues & Students



A. Lakhtakia Physical Vapor Deposition (Columnar Thin Films)





Vapor flux

Oblique

columns



A. Lakhtakia Physical Vapor Deposition (Sculptured Thin Films)





Rotate about y axis for nematic morphology

Rotate about z axis for helicoidal morphology

Mix and match rotations for complex morphologies

A. Lakhtakia (Serial Bideposition)







Sculptured Thin Films

Optical Devices:

Bacterial Sensors (Penn State) Light Sources (Penn State)

Polarization Filters

Ultranarrowband Filters

Fluid Concentration Sensors

Bragg Filters

Biomedical Applications:

Other Applications:

Tissue Scaffolds (Penn State) Stents (Penn State) Bone Repair (Penn State)

Photocatalysis (Toyota) Thermal Barriers (Alberta) Energy Harvesting (Penn State, Toledo)



OPTICAL MODELING



A. Lakhtakia Optical Modeling of STFs



Introduction to Complex Mediums for Optics and Electromagnetics

Editors: Werner S. Weiglhofer • Akhlesh Lakhtakia



Linear Bianisotropic Materials

SPIE Press (2003)

Lakhtakia Optical Modeling of STFs

$$D(\mathbf{r}, \omega) = \epsilon_0 \underline{S}(z) \cdot \left[\underline{\epsilon}_{ref}(\omega) \cdot \underline{S}^T(z) \cdot \mathbf{E}(\mathbf{r}, \omega) + \underline{\alpha}_{ref}(\omega) \cdot \underline{S}^T(z) \cdot \mathbf{H}(\mathbf{r}, \omega) \right], \quad \text{Linear}$$

$$\mathbf{B}(\mathbf{r},\omega) = \mu_0 \underline{\underline{S}}(z) \cdot \left[\underline{\underline{\beta}}_{ref}(\omega) \cdot \underline{\underline{S}}^T(z) \cdot \mathbf{E}(\mathbf{r},\omega) + \underline{\underline{\mu}}_{ref}(\omega) \cdot \underline{\underline{S}}^T(z) \cdot \mathbf{H}(\mathbf{r},\omega)\right],$$

Linear Bianisotropic Materials



PENNSTATE

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1.8 5 5

Introduction to Complex Mediums for Optics and Electromagnetics

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$$\begin{split} \underline{\underline{S}}_{x}(z) &= \mathbf{u}_{x}\mathbf{u}_{x} + (\mathbf{u}_{y}\mathbf{u}_{y} + \mathbf{u}_{z}\mathbf{u}_{z})\,\cos\,\xi(z) \\ &+ (\mathbf{u}_{z}\mathbf{u}_{y} - \mathbf{u}_{y}\mathbf{u}_{z})\,\sin\,\xi(z)\,,\\ \underline{\underline{S}}_{y}(z) &= \mathbf{u}_{y}\mathbf{u}_{y} + (\mathbf{u}_{x}\mathbf{u}_{x} + \mathbf{u}_{z}\mathbf{u}_{z})\,\cos\,\tau(z) \\ &+ (\mathbf{u}_{z}\mathbf{u}_{x} - \mathbf{u}_{x}\mathbf{u}_{z})\,\sin\,\tau(z)\,,\\ \underline{\underline{S}}_{z}(z) &= \mathbf{u}_{z}\mathbf{u}_{z} + (\mathbf{u}_{x}\mathbf{u}_{x} + \mathbf{u}_{y}\mathbf{u}_{y})\,\cos\,\zeta(z) \\ &+ (\mathbf{u}_{y}\mathbf{u}_{x} - \mathbf{u}_{x}\mathbf{u}_{y})\,\sin\,\zeta(z)\,. \end{split}$$

SPIE Press (2003)



A. Lakhtakia Optical Modeling of STFs

Dielectric Materials

$$\begin{aligned} \mathbf{D}(\mathbf{r},\omega) &= \epsilon_0 \, \underline{\epsilon}_r \, (z,\omega) \, \bullet \, \mathbf{E}(\mathbf{r},\omega) \\ &= \epsilon_0 \, \underline{\underline{S}}(z) \, \bullet \, \underline{\underline{S}}_{ref}(\omega) \, \bullet \, \underline{\underline{S}}^T(z) \, \bullet \, \mathbf{E}(\mathbf{r},\omega) \,, \\ \mathbf{B}(\mathbf{r},\omega) &= \mu_0 \, \mathbf{H}(\mathbf{r},\omega) \,. \end{aligned}$$



A. Lakhtakia Optical Modeling of STFs

Locally Orthorhombic Materials

$$\begin{split} \mathbf{D}(\mathbf{r},\omega) &= \epsilon_0 \, \underline{\underline{\epsilon}}_r \left(z, \omega \right) \, \bullet \, \mathbf{E}(\mathbf{r},\omega) \\ &= \epsilon_0 \, \underline{\underline{S}}(z) \, \bullet \, \underline{\underline{S}}^T(\omega) \, \bullet \, \underline{\underline{S}}^T(z) \, \bullet \, \mathbf{E}(\mathbf{r},\omega) \, , \\ \mathbf{B}(\mathbf{r},\omega) &= \mu_0 \, \mathbf{H}(\mathbf{r},\omega) \, . \end{split}$$

$$\underline{\underline{\epsilon}}_{ref}(\omega) = \underline{\underline{\hat{S}}}_{y}(\chi) \bullet \underline{\underline{\hat{S}}}_{ref}^{o}(\omega) \bullet \underline{\underline{\hat{S}}}_{y}^{T}(\chi)$$

$$\underline{\epsilon}_{ref}^{o}(\omega) = \underline{\epsilon}_{ref}(\omega) \Big|_{\chi=0} = \epsilon_{a}(\omega) \mathbf{u}_{z} \mathbf{u}_{z} + \epsilon_{b}(\omega) \mathbf{u}_{x} \mathbf{u}_{x} + \epsilon_{c}(\omega) \mathbf{u}_{y} \mathbf{u}_{y}$$

$$\underline{\hat{S}}_{y}(\chi) = \mathbf{u}_{y}\mathbf{u}_{y} + (\mathbf{u}_{x}\mathbf{u}_{x} + \mathbf{u}_{z}\mathbf{u}_{z})\cos\chi + (\mathbf{u}_{z}\mathbf{u}_{x} - \mathbf{u}_{x}\mathbf{u}_{z})\sin\chi$$



 γ_{τ}



Homogenize a collection of parallel ellipsoids to get $\underline{\epsilon}_{ref}^{o}(\omega)$



Sherwin and Lakhtakia (2001-2003): Bruggeman formalism

Mathematica Program



A. Lakhtakia Optical Modeling of STFs Wave Propagation

$$\begin{split} \mathbf{E}(\mathbf{r},\omega) &= \mathbf{e}(z,\kappa,\psi,\omega)\,\exp\left[i\kappa(x\cos\psi+y\sin\psi)\right]\\ \mathbf{H}(\mathbf{r},\omega) &= \mathbf{h}(z,\kappa,\psi,\omega)\,\exp\left[i\kappa(x\cos\psi+y\sin\psi)\right] \end{split}$$

$$\nabla \times \mathbf{E}(\mathbf{r}, \omega) = i\omega \mathbf{B}(\mathbf{r}, \omega) ,$$
$$\nabla \times \mathbf{H}(\mathbf{r}, \omega) = -i\omega \mathbf{D}(\mathbf{r}, \omega) ,$$



Akhlesh Lakhtakia Russell Messier

$$\frac{d}{dz} \left[\mathbf{f}(z,\kappa,\psi,\omega) \right] = i [\mathbf{P}(z,\kappa,\psi,\omega)] \left[\mathbf{f}(z,\kappa,\psi,\omega) \right].$$

$$[\mathbf{f}(z,\kappa,\psi,\omega)] = \begin{bmatrix} e_x(z,\kappa,\psi,\omega) \\ e_y(z,\kappa,\psi,\omega) \\ h_x(z,\kappa,\psi,\omega) \\ h_y(z,\kappa,\psi,\omega) \end{bmatrix}$$

Mathematica Program



EXAMPLES OF POLARIZATION ENGINEERING

Chiral STFs: Circular Bragg Phenomenon







- A simple explanation (Coupled-Wave Theory):
- Co-handed wave: Scalar Bragg grating
- Cross-handed wave: Homogeneous bulk medium



Chiral STF as CP Filter

442. J.A. Sherwin, A. Lakhtakia & I.J. Hodgkinson, 'On calibration of a nominal structure--property relationship model for chiral sculptured thin films by axial transmittance measurements,' *Optics Communications*, **209**, 2002, 369–375.



Figure 10.2: Predicted and measured transmittances of a circular polarization filter as functions of the free-space wavelength λ_0 for normal incidence. The filter is a chiral STF of patinal titanium oxide. The reference permittivity dyadic was predicted with $\epsilon_s = 6.3 + i0.012$, $\epsilon_v = 1$, $f_v = 0.421$, $\gamma_\tau^{(s)} = \gamma_\tau^{(v)} = 20$, and $\gamma_b^{(s)} = \gamma_b^{(v)} = 1.06$ set in Program 6.1. The other parameters are $\chi = 47 \text{ deg}$, h = -1, $\Omega = 173 \text{ nm}$, $L = 30 \Omega$, and $\psi = 0 \text{ deg}$. (Adapted from Sherwin et al. [109] with permission of Elsevier.)



Engineering of Bragg Regime and CP State

$$\underline{\underline{\epsilon}}_{chiral}(z,\omega) = \underline{\underline{S}}_{z}(z) \cdot \underline{\underline{S}}_{y}(\chi) \cdot [\epsilon_{a}(\omega) \,\hat{\mathbf{u}}_{z} \,\hat{\mathbf{u}}_{z} + \epsilon_{b}(\omega) \,\hat{\mathbf{u}}_{x} \hat{\mathbf{u}}_{x} + \epsilon_{c}(\omega) \,\hat{\mathbf{u}}_{y} \hat{\mathbf{u}}_{y}] \cdot \underline{\underline{S}}_{y}^{-1}(\chi) \cdot \underline{\underline{S}}_{z}^{-1}(z)$$

$$\underline{\underline{S}}_{z}(z) = (\hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{x} + \hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{y})\cos(\pi z/\Omega) + h(\hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{x} - \hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{y})\sin(\pi z/\Omega) + \hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{z}$$

$$\underline{\underline{S}}_{y}(\chi) = \hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{y} + (\hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{x} + \hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{z})\cos\chi + (\hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{x} - \hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{z})\sin\chi$$



Engineering of Bragg Regime and CP State

$$\underline{\underline{\epsilon}}_{chiral}(z,\omega) = \underline{\underline{S}}_{z}(z) \cdot \underline{\underline{S}}_{y}(\chi) \cdot [\epsilon_{a}(\omega) \,\hat{\mathbf{u}}_{z} \,\hat{\mathbf{u}}_{z} + \epsilon_{b}(\omega) \,\hat{\mathbf{u}}_{x} \hat{\mathbf{u}}_{x} + \epsilon_{c}(\omega) \,\hat{\mathbf{u}}_{y} \hat{\mathbf{u}}_{y}] \cdot \underline{\underline{S}}_{y}^{-1}(\chi) \cdot \underline{\underline{S}}_{z}^{-1}(z)$$

$$\underline{\underline{S}}_{z}(z) = (\hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{x} + \hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{y})\cos(\pi z/\Omega) + h(\hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{x} - \hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{y})\sin(\pi z/\Omega) + \hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{z}$$

$$\underline{\underline{S}}_{y}(\chi) = \hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{y} + (\hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{x} + \hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{z})\cos\chi + (\hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{x} - \hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{z})\sin\chi$$

Rotational Speed: Controls Ω

Rotational Sense: Controls h

Vapor Incidence Angle: Controls $\epsilon_{a,b,c}$ and χ



Chiral STF as CP Filter

Post-Deposition Engineering of Bragg Regime

558. S.M. Pursel, M.W. Horn & A. Lakhtakia, Blue-shifting of circular Bragg phenomenon by annealing of chiral sculptured thin films,' *Optics Express*, 14, 2006, 8001 – 8012.





Post-Deposition Engineering of Bragg Regime

Annealing

<u>Blue-shift factors:</u> (i) Decreases pitch (ii) Thins nanowires

<u>Red-shift factors:</u> (i) Increases permittivity





Spectral Hole Filter

Central Phase Defect in a Chiral STF

- Homogeneous-layer defect - Isotropic - Anisotropic

- Twist defect

- Structurally-chiral-layer defect











Spectral Hole Filter

Defect-free





Co-handed Cross-handed Theory/Experiment Theory only

Thick Chiral STF Transmission Hole Cross-handed Theory only



Spectral Hole Filter

Isotropic-layer defect



Figure 10.10: Measured transmittances of a narrow bandpass filter comprising an isotropic homogeneous spacer of hafnium oxide interposed between two identical, structurally left-handed, chiral STF sections of titanium oxide. Evidence of a hole in the spectrum of R_{LL} at 580-nm wavelength is provided by the spectrum of T_{LL} . (Adapted from Hodgkinson et al. [125] with permission of Elsevier.)

377. I.J. Hodgkinson, Q.h. Wu, A. Lakhtakia & M.W. McCall, 'Spectral-hole filter fabricated using sculptured thin-film technology,' *Optics Communications*, 177, 2000, 79–84.



Spectral Hole Filter

Twist defect



Fig. 7. (a) Measured spectra of the transmittances, T_{RR} , T_{RL} , T_{LR} and T_{LL} of the spacerless filter sp290200 with twist $\psi_t = 90^\circ$. (b) Transmittance spectrums simulated for the above filter using the parameters h = -1, N = 6, $\Omega = 163$ nm, $n_{av} = 1.914$ and $\Delta n = 0.116$, so that $\lambda_0^{Br} = 622$ nm.

388. I.J. Hodgkinson, Q.h. Wu, K.E. Thorn, A. Lakhtakia & M.W. McCall, 'Spacerless circular-polarization spectral-hole filters using chiral sculptured thin films: theory and experiment,' *Optics Communications*, 184, 2000, 57–66.



Spectral Hole Filter

Post-Deposition Engineering

Chemical Etching



Pursel, Lakhtakia, and Horn, Optical Engineering (2007)



Spectral Hole Filter

Post-Deposition Engineering

Chemical Etching Columnar Thinning Blue Shift



Pursel, Lakhtakia, and Horn, Optical Engineering (2007)



A. Lakhtakia Fluid Concentration Sensor



Figure 10.22: Optical response of a narrow bandpass filter, described by Eq. (10.17) and made of two structurally left-handed chiral STF sections, on infiltration by water vapor. The dotted lines indicate the measured transmittance spectrum when the filter was dry. The filter was flooded with water and then allowed to recover by evaporation in air. Transmittance spectrums recorded at 5-s intervals after the flooding are shown. (Adapted from Lakhtakia et al. [105] with permission of Elsevier.)

410. A. Lakhtakia, M.W. McCall, J.A. Sherwin, Q.H. Wu & I.J. Hodgkinson, 'Sculptured-thin-film spectral holes for optical sensing of fluids,' *Optics Communications*, 194, 2001, 33–46.



MORE EXAMPLES OF POLARIZATION ENGINEERING



Tilt-Modulated Chiral STF

 $\underline{\epsilon}_{tmc}(z,\omega) = \underline{\underline{S}}_{z}(z) \cdot \underline{\underline{S}}_{y}[\chi(z)] \cdot [\epsilon_{a}(z,\omega) \,\hat{\mathbf{u}}_{z} \hat{\mathbf{u}}_{z} + \epsilon_{b}(z,\omega) \,\hat{\mathbf{u}}_{x} \hat{\mathbf{u}}_{x} + \epsilon_{c}(z,\omega) \,\hat{\mathbf{u}}_{y} \hat{\mathbf{u}}_{y}] \cdot \underline{\underline{S}}_{y}^{-1}[(\chi(z)] \cdot \underline{\underline{S}}_{z}^{-1}(z)]$



 $\chi_v(z) = \tilde{\chi}_v + \delta_v \sin(2\pi z / \Omega)$

500. J.A. Polo, Jr. & A. Lakhtakia, 'Tilt-modulated chiral sculptured thin films: an alternative to quarter-wave stacks,' *Optics Communications*, **242**, 2004, 13 – 21.



Tilt-Modulated Chiral STF

Ordinary Dielectric Mirror



Advantages:

(1) Single material

(2) Bragg FWHM governed by tilt-modulation amplitude



Ambichiral STF

Reusch 1869

$$\underline{\underline{\epsilon}}_{n}(\omega) = \underline{\underline{R}}_{z} \left[2h \frac{(n-1)\pi}{N} \right] \cdot \underline{\underline{S}}_{y}(\chi) \cdot \left[\epsilon_{a}(\omega) \,\hat{\mathbf{u}}_{z} \,\hat{\mathbf{u}}_{z} + \epsilon_{b}(\omega) \,\hat{\mathbf{u}}_{x} \hat{\mathbf{u}}_{x} + \epsilon_{c}(\omega) \,\hat{\mathbf{u}}_{y} \hat{\mathbf{u}}_{y} \right] \cdot \underline{\underline{S}}_{y}^{-1}(\chi) \cdot \underline{\underline{R}}_{z}^{-1} \left[2h \frac{(n-1)\pi}{N} \right]_{(1-1)} \left[2h \frac{(n-1)\pi}{N} \right$$

 $\underline{\underline{R}}_{z}(\zeta) = (\hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{x} + \hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{y})\,\cos\zeta + (\hat{\mathbf{u}}_{y}\hat{\mathbf{u}}_{x} - \hat{\mathbf{u}}_{x}\hat{\mathbf{u}}_{y})\,\sin\zeta + \hat{\mathbf{u}}_{z}\hat{\mathbf{u}}_{z}$



$$d_n = d_1 \left\{ 1 + a \sin \left[4 \frac{(n-1)\pi}{N} \right] \right\} \,, \quad 0 \le a \le 1$$



Ambichiral STF

All layers of equal thickness.

2 Bragg regimes

Different CP states reflected



Fig. 4. Measured co-polarized transmittances of an ambichiral layered structure characterized by h=-1, N=10q, and q=4. This structure of titanium oxide was created using the serial bideposition technique.

497. I.J. Hodgkinson, A. Lakhtakia, Q.h. Wu, L. De Silva & M.W. McCall, 'Ambichiral, equichiral and finely chiral layered structures,' *Optics Communications*, 239, 2004, 353 – 358.



Ambichiral STF

Layers of unequal thickness.

$$d_n = d_1 \left\{ 1 + a \sin \left[4 \frac{(n-1)\pi}{N} \right] \right\} \,, \quad 0 \le a \le 1$$

1 Bragg regime

544. B.M. Ross, A. Lakhtakia & I.J. Hodgkinson, 'Towards the design of ellipticalpolarization rejection filters,' *Optics Communications*, **259**, 2006, 479 – 483.



Ambichiral STF

Layers of unequal thickness.

1 Bragg regime

EP states (Ψ and δ) reflected

Better for CP and nearly CP states

544. B.M. Ross, A. Lakhtakia & I.J. Hodgkinson, 'Towards the design of ellipticalpolarization rejection filters,' *Optics Communications*, **259**, 2006, 479 – 483.





WHAT's NEXT?

STFs on Microscale Topography (Cross-sectional SEMs of SiOx STFs)









Chromium



Metal STFs on Topography



Molybdenum



Aluminum



Semiconductor STFs on Micro and Nanoscale Topography



SnO_x STFs grown on photoresist patterns

Sculptured Nanowires on Nanoscale Topography



Single SiOx nanowire array grown on 60 nm ebeam resist



BCC array of SiOx nanocolumns



HCP array of SiOx nanocolumns



1um x 1um mesh of SiOx nanolines

INSTITUTE OF PHYSICS PUBLISHING

Nanotechnology 15 (2004) 303-310

NAMOTECHNOLOGY

PII: S0957-4484(04)69259-2

Blending of nanoscale and microscale in uniform large-area sculptured thin-film architectures

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Selective growth of sculptured nanowires on microlithographic lattices

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We have grown helicoidal nanowire assemblies on a variety of topographic substrates with regular microlithographic patterns, thereby demonstrating that sculptured thin films with transversely latticed architecture can be grown by physical vapor deposition. The transverse feature-separations are as low as 100–300 nm, and mesa regions are circular posts as small as 60 nm in diameter. The initial as well as the subsequent stages of growth on topographic substrates can be understood using simple geometric shadowing arguments. © 2004 American Vacuum Society.



Thesis

Morphology can be nanoengineered

to obtain

desired polarization & operating frequency band

